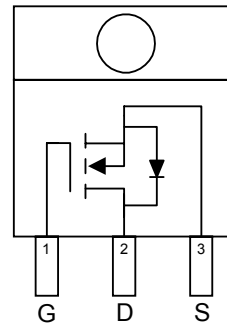


## N-Channel Enhancement Mode MOSFET

### Features

- 30V / 80A ,  $R_{DS(ON)} = 5.5m\Omega(\text{typ.}) @ V_{GS} = 10V$   
 $R_{DS(ON)} = 8.5m\Omega(\text{typ.}) @ V_{GS} = 4.5V$
- Super High Dense Advanced Cell Design for Extremely Low  $R_{DS(ON)}$
- Reliable and Rugged
- TO-220 , TO-252 and TO-263 Packages

### Pin Description




Top View of TO-220, TO-252 and TO-263

### Applications

- Power Management in Desktop Computer or DC/DC Converters.

### Ordering and Marking Information

<p>APM3007N □□-□□</p> <p>□□ - Handling Code</p> <p>□□ - Temp. Range</p> <p>□□ - Package Code</p>	<p>Package Code</p> <p>F : TO-220    G : TO-263    U : TO-252</p> <p>Operating Junction Temp. Range</p> <p>C : -55 to 125°C</p> <p>Handling Code</p> <p>TU : Tube</p> <p>TR : Tape &amp; Reel</p>
<p>APM3007N F/G/U : </p>	<p>XXXXX - Date Code</p>

### Absolute Maximum Ratings $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$I_D^*$	Maximum Drain Current – Continuous	70	A
$I_{DM}$	Maximum Drain Current – Pulsed	130	

\* Surface Mounted on FR4 Board,  $t \leq 10$  sec.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

## Absolute Maximum Ratings Cont. (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit		
P <sub>D</sub>	Maximum Power Dissipation	T <sub>A</sub> =25°C	TO-252	50	W
			TO-263	62.5	
		T <sub>A</sub> =100°C	TO-252	20	
			TO-263	25	
T <sub>J</sub> , T <sub>STG</sub>	Maximum Operating and Storage Junction Temperature	-55 to 150	°C		
R <sub>θJA</sub>	Thermal Resistance – Junction to Ambient	TO-252	50	°C/W	
		TO-263	60		
R <sub>θJC</sub>	Thermal Resistance – Junction to Case	TO-252	2.5	°C/W	
		TO-263	2		

## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	APM3007N			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V			1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA	1		3	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
R <sub>DS(ON)</sub> <sup>a</sup>	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =40A		5.5	7	mΩ
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =20A		8.5	10	
V <sub>SD</sub> <sup>a</sup>	Diode Forward Voltage	I <sub>SD</sub> =35A, V <sub>GS</sub> =0V	0.6		1.3	V
<b>Dynamic<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>DS</sub> =40A		25	30	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> =4.5V,		12		
Q <sub>gd</sub>	Gate-Drain Charge			8		
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> =15V, I <sub>DS</sub> =1A, V <sub>GEN</sub> =10V, R <sub>G</sub> =0.2Ω		13	20	ns
T <sub>r</sub>	Turn-on Rise Time			9	15	
t <sub>d(OFF)</sub>	Turn-off Delay Time			43	66	
T <sub>f</sub>	Turn-off Fall Time			14	28	
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V		3000		pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V		660		
C <sub>rss</sub>	Reverse Transfer Capacitance	Frequency=1.0MHz		330		

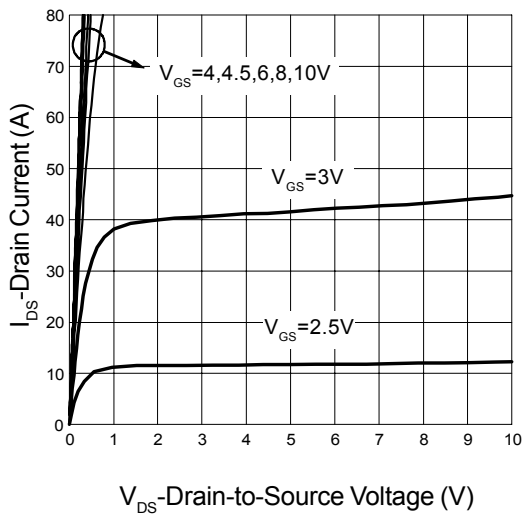
### Notes

<sup>a</sup> : Pulse test ; pulse width ≤300μs, duty cycle ≤ 2%

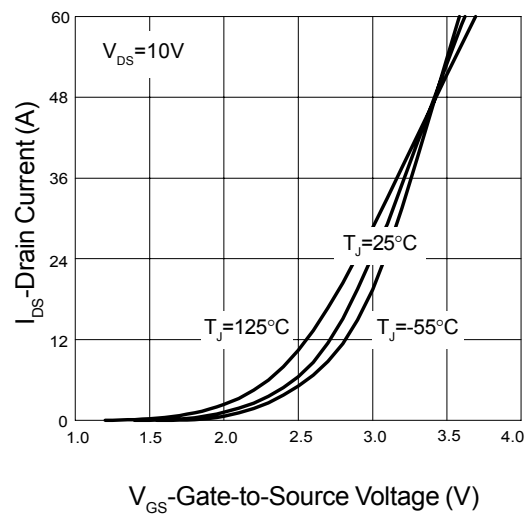
<sup>b</sup> : Guaranteed by design, not subject to production testing

Typical Characteristics

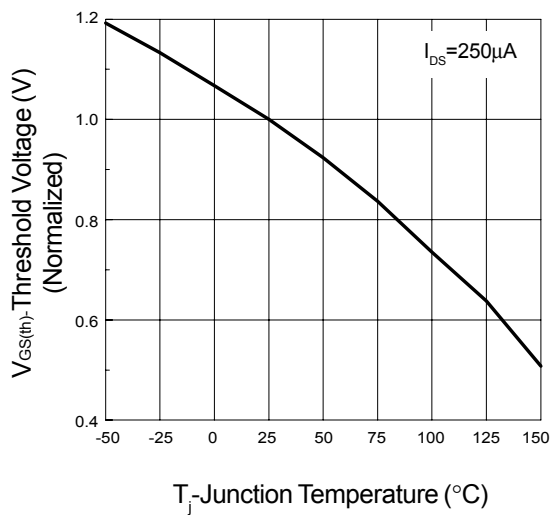
Output Characteristics



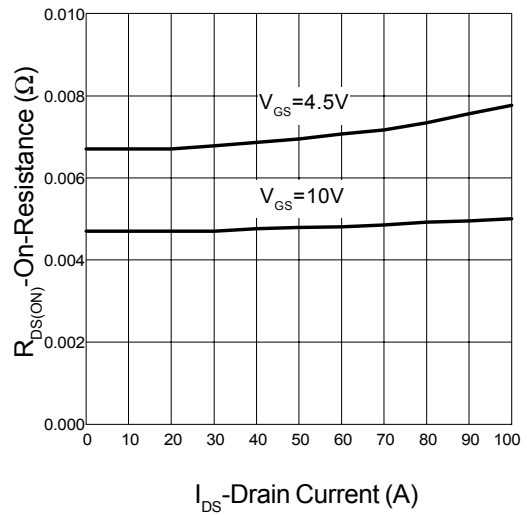
Transfer Characteristics



Threshold Voltage vs. Junction Temperature

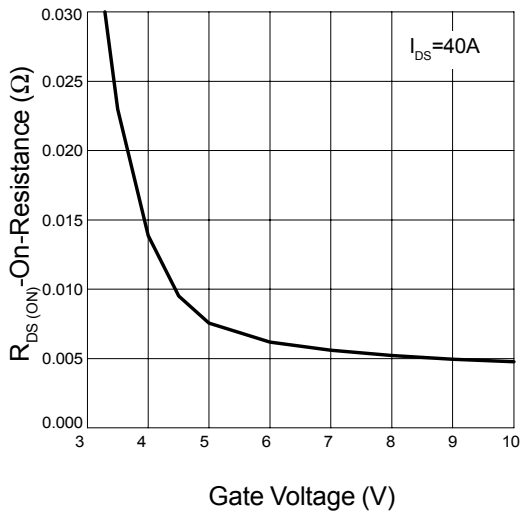


On-Resistance vs. Drain Current

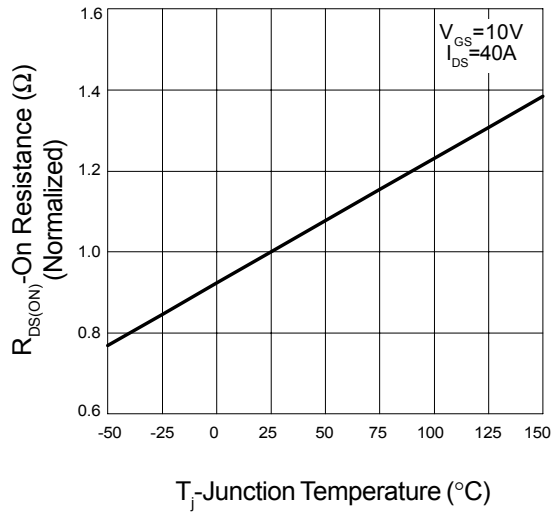


Typical Characteristics Cont.

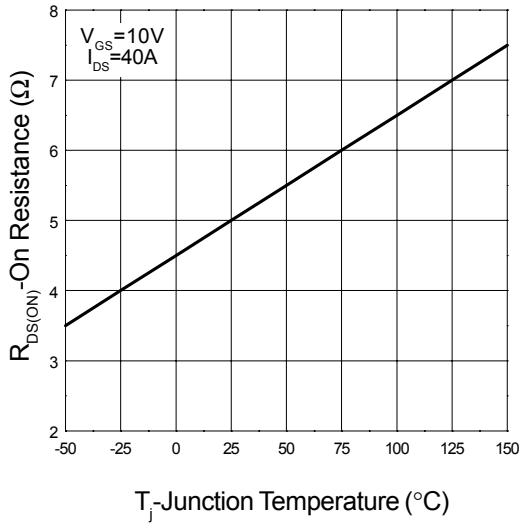
On-Resistance vs. Gate-to-Source Voltage



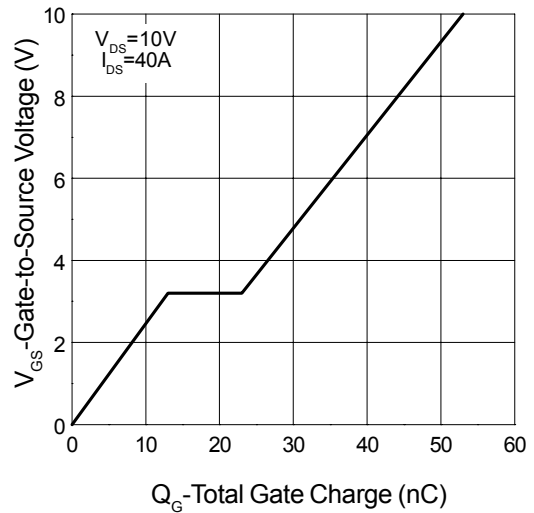
On-Resistance vs. Junction Temperature



On-Resistance vs. Junction Temperature

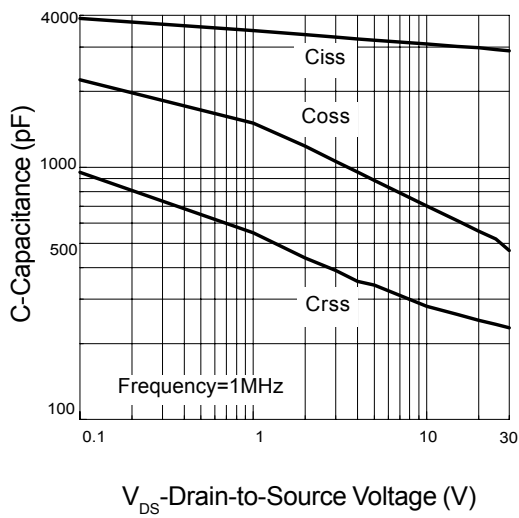


Gate Charge

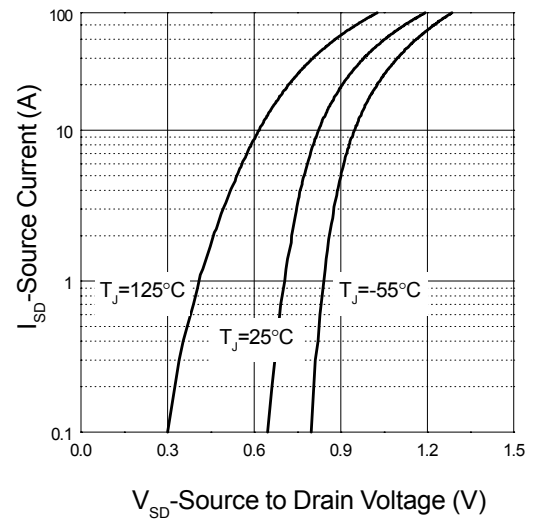


Typical Characteristics Cont.

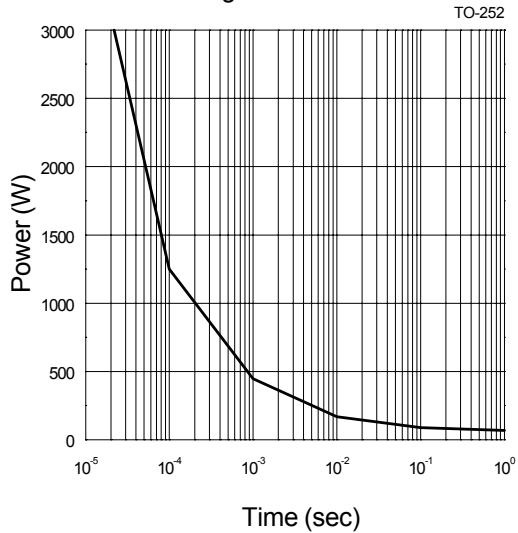
Capacitance Characteristics



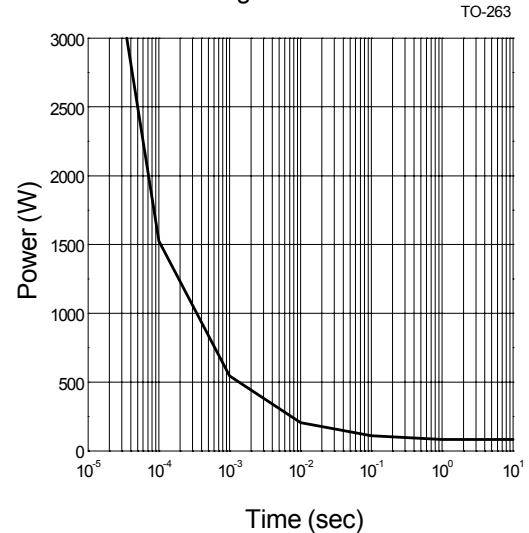
Source-Drain Diode Forward Voltage



Single Pulse Power TO-252

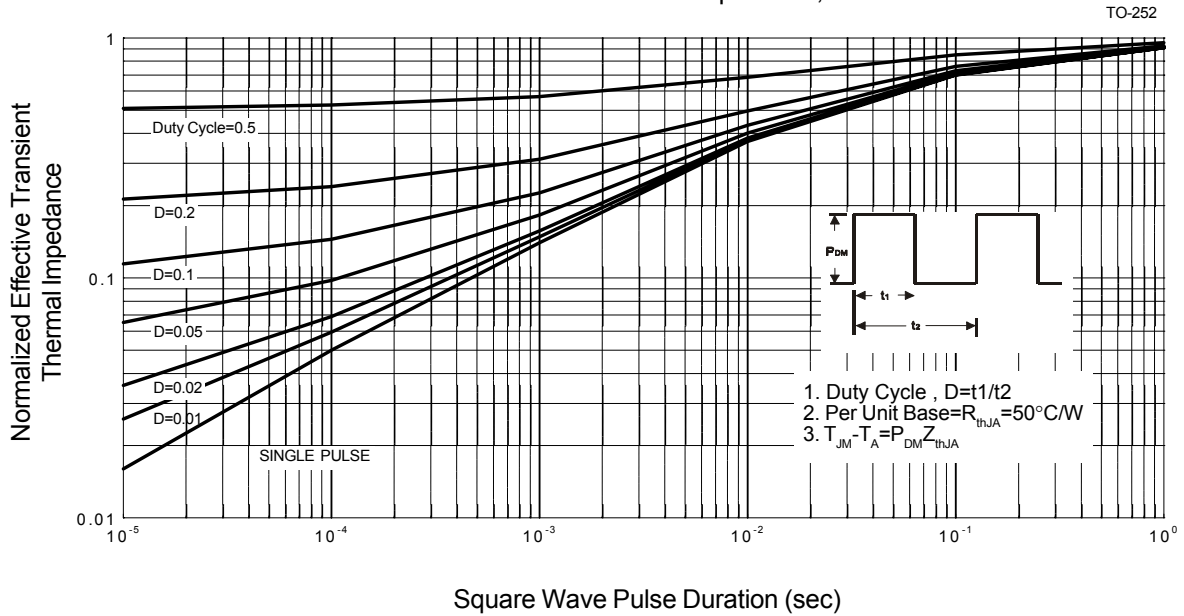


Single Pulse Power TO-263

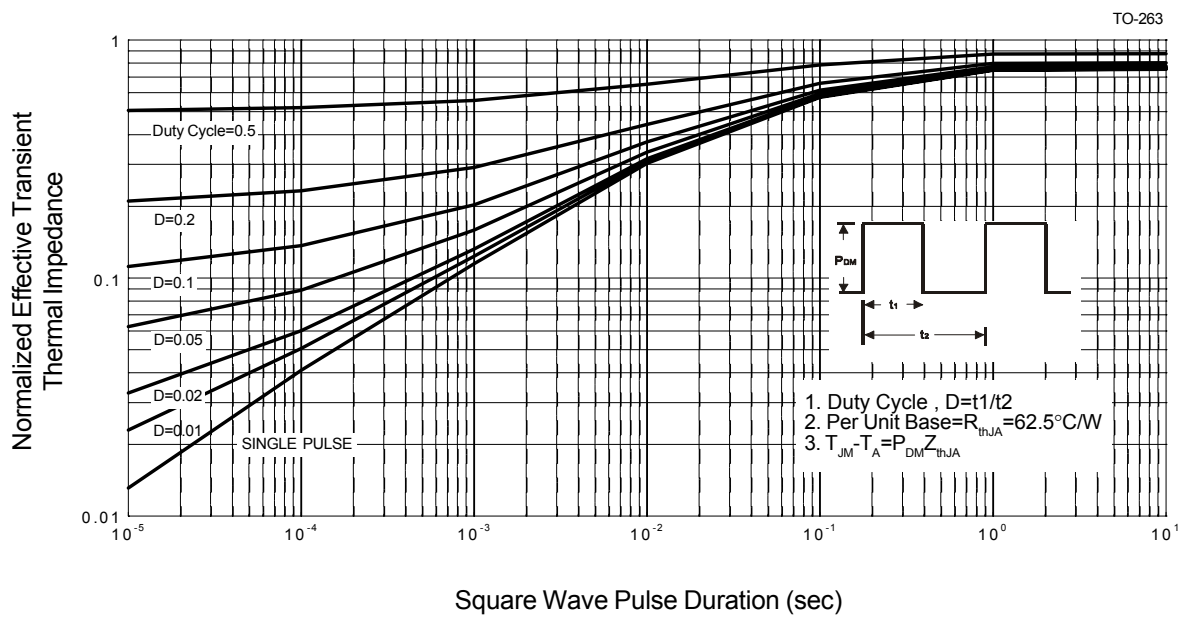


Typical Characteristics Cont.

Normalized Transient Thermal Impedance, Junction to Ambient

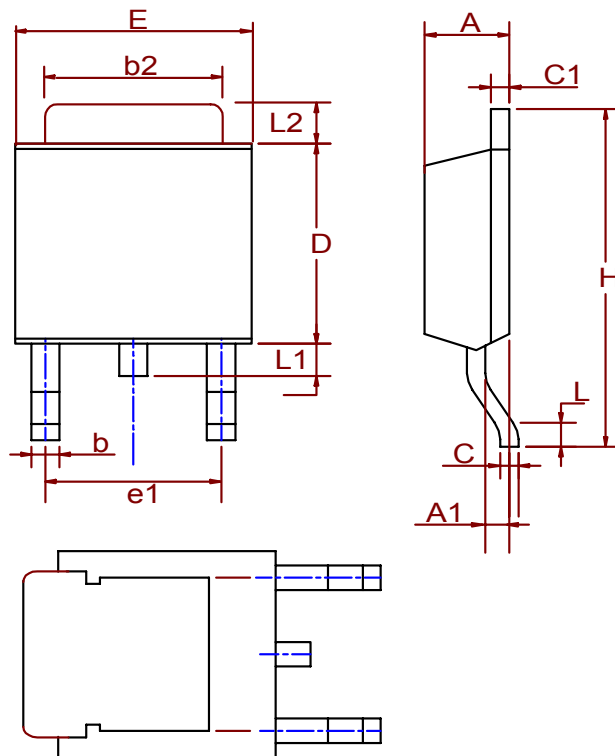


Normalized Transient Thermal Impedance, Junction to Ambient



**Package Informaion**

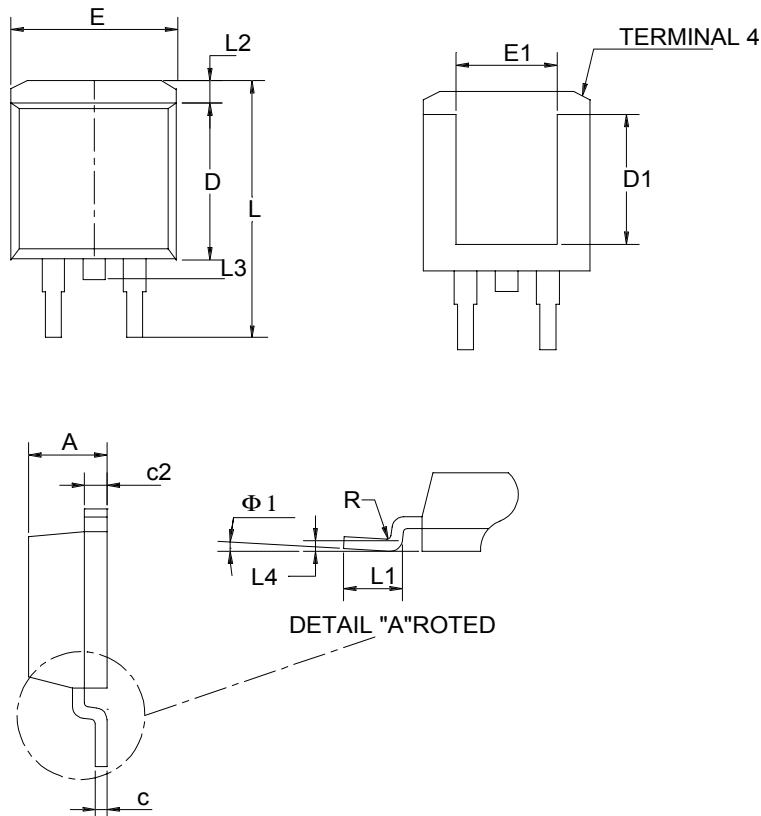
TO-252( Reference JEDEC Registration TO-252)



Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
E	6.35	6.73	0.250	0.265
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080

## Packaging Information Cont.

TO-263 ( Reference JEDEC Registration TO-263)

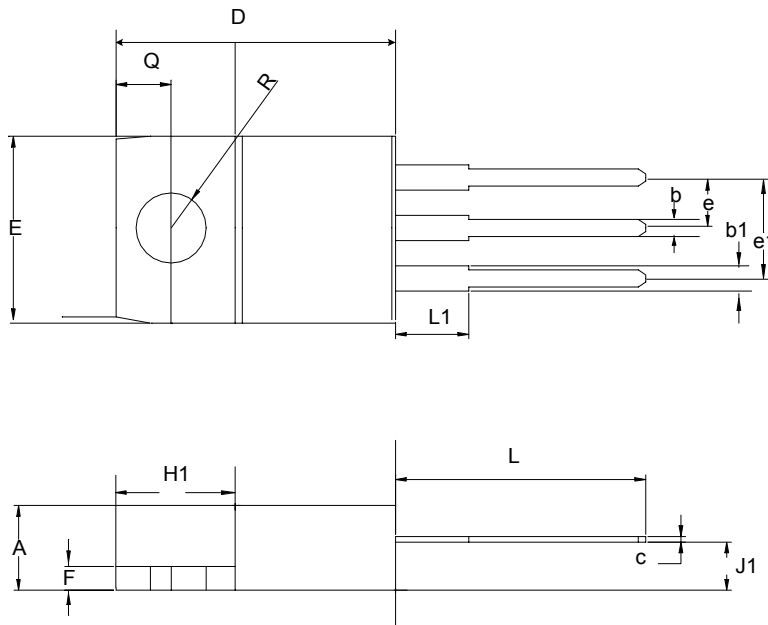


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	0.160	0.190
b	0.51	1.016	0.02	0.040
b2	1.14	1.651	0.045	0.065
c	0.38 TYP.		0.015 TYP.	
c2	1.14	1.40	0.045	0.055
D	8.64	9.65	0.340	0.380
E	9.65	10.54	0.380	0.415
L	14.60	15.88	0.575	0.625
L1	2.24	2.84	0.090	0.110
L2	1.02	2.92	0.040	0.112
L3	1.20	1.78	0.050	0.070



**Package Information Cont.**

TO-220 ( Reference JEDEC Registration TO-220)



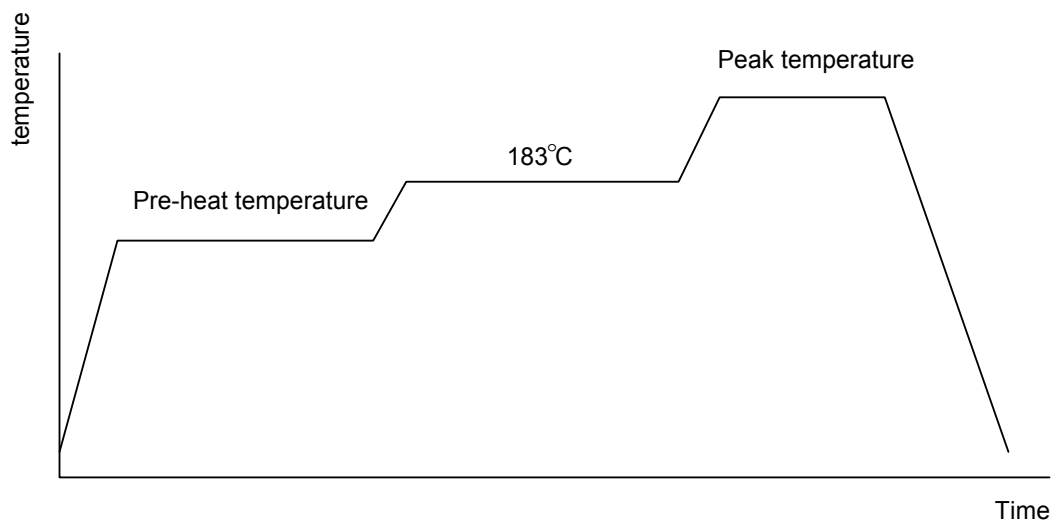
Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.56	4.83	0.140	0.190
b1	1.14	1.78	0.045	0.070
b	0.51	1.14	0.020	0.045
c	0.31	1.14	0.012	0.045
D	14.23	16.51	0.560	0.650
e	2.29	2.79	0.090	0.110
e1	4.83	5.33	0.190	0.210
E	9.65	10.67	0.380	0.420
F	0.51	1.40	0.020	0.055
H1	5.84	6.86	0.230	0.270
J1	2.03	2.92	0.080	0.115
L	12.7	14.73	0.500	0.580
L1	3.65	6.35	0.143	0.250
R	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

## Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb)
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

## Reflow Condition (IR/Convection or VPR Reflow)

Reference JEDEC Standard J-STD-020A APRIL 1999



## Classification Reflow Profiles

	Convection or IR/ Convection	VPR
Average ramp-up rate(183 °C to Peak)	3°C/second max.	10 °C /second max.
Preheat temperature 125 ± 25 °C)	120 seconds max.	
Temperature maintained above 183 °C	60 ~ 150 seconds	
Time within 5 °C of actual peak temperature	10 ~ 20 seconds	60 seconds
Peak temperature range	220 +5/-0 °C or 235 +5/-0 °C	215~ 219 °C or 235 +5/-0 °C
Ramp-down rate	6°C /second max.	10 °C /second max.
Time 25 °C to peak temperature	6 minutes max.	

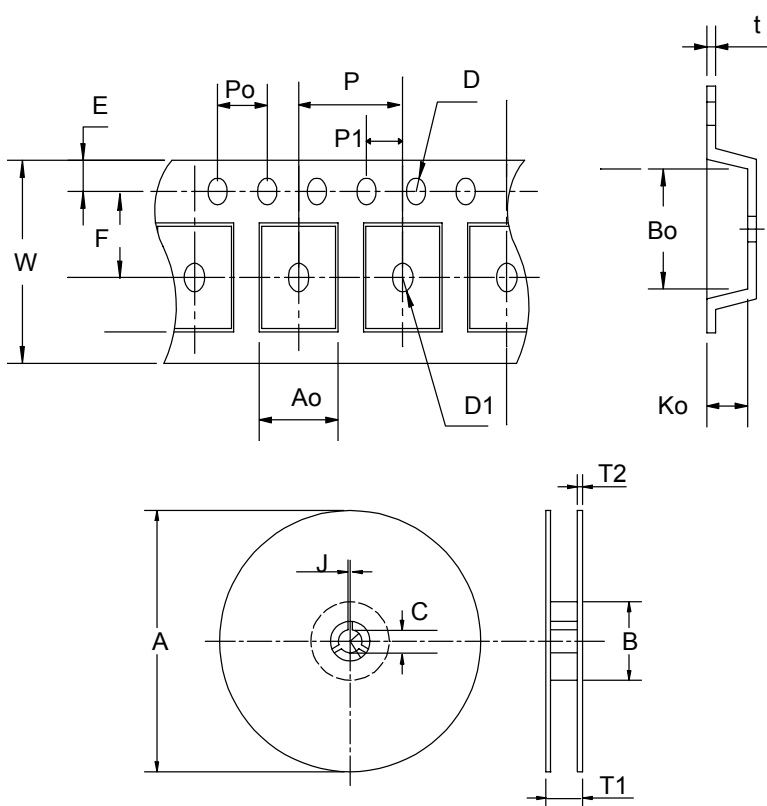
## Package Reflow Conditions

pkg. thickness ≥ 2.5mm and all bags	pkg. thickness < 2.5mm and pkg. volume ≥ 350 mm	pkg. thickness < 2.5mm and pkg. volume <
Convection 220 +5/-0 °C		Convection 235 +5/-0 °C
VPR 215-219 °C		VPR 235 +5/-0 °C
IR/Convection 220 +5/-0 °C		IR/Convection 235 +5/-0 °C

## Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

## Carrier Tape & Reel Dimension



<b>Application</b>	A	B	C	J	T1	T2	W	P	E
<b>TO-252</b>	330±3	100±2	13±0.5	2±0.5	16.4 <sup>+0.3</sup> <sub>-0.2</sub>	2.5±0.5	16 <sup>+0.3</sup> <sub>16-0.1</sub>	8±0.1	1.75±0.1
<b>Application</b>	F	D	D1	Po	P1	Ao	Bo	Ko	t
<b>TO-252</b>	7.5±0.1	1.5±0.1	1.5±0.25	4.0±0.1	2.0±0.1	6.8±0.1	10.4±0.1	2.5±0.1	0.3±0.05
<b>Application</b>	A	B	C	J	T1	T2	W	P	E
<b>TO-263</b>	380±3	80±2	13±0.5	2±0.5	24±4	2±0.3	24 <sup>+0.3</sup> <sub>-0.1</sub>	16±0.1	1.75±0.1
<b>Application</b>	F	D	D1	Po	P1	Ao	Bo	Ko	t
<b>TO-263</b>	11.5±0.1	1.5±0.1	1.5±0.25	4.0±0.1	2.0±0.1	10.8±0.1	16.1±0.1	5.2±0.1	0.35±0.013

(mm)

## Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO- 252	16	13.3	2500
TO- 263	24	21.3	1000

## Customer Service

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